## NSN 5961-01-046-9585

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Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-046-9585 **Inclosure Material:** Metal **Overall Length:** 1.736 inches **Mounting Facility Quantity: Mounting Method:** Threaded stud **Overall Width Across Flats:** Between 0.544 inches and 0.563 inches **Thread Size:** 0.250 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 500.0 nonrepetitive peak reverse voltage and 400.0 repetitive peak reverse voltage and 400.0 repetitive peak off-state voltage and 5.0 peak gate voltage **Current Rating Per Characteristic:** 16.00 amperes forward current, total rms megahertz and 150.00 amperes peak forward surge current nanoamperes **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius ambient air **Test Data Document:** 81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 threaded stud and 2 tab, solder lug **Specification Data:** 81349-mil-s-19500/108 government specification Shelf Life: N/a **Unit Of Measure:** Demilitarization: No Fiig: